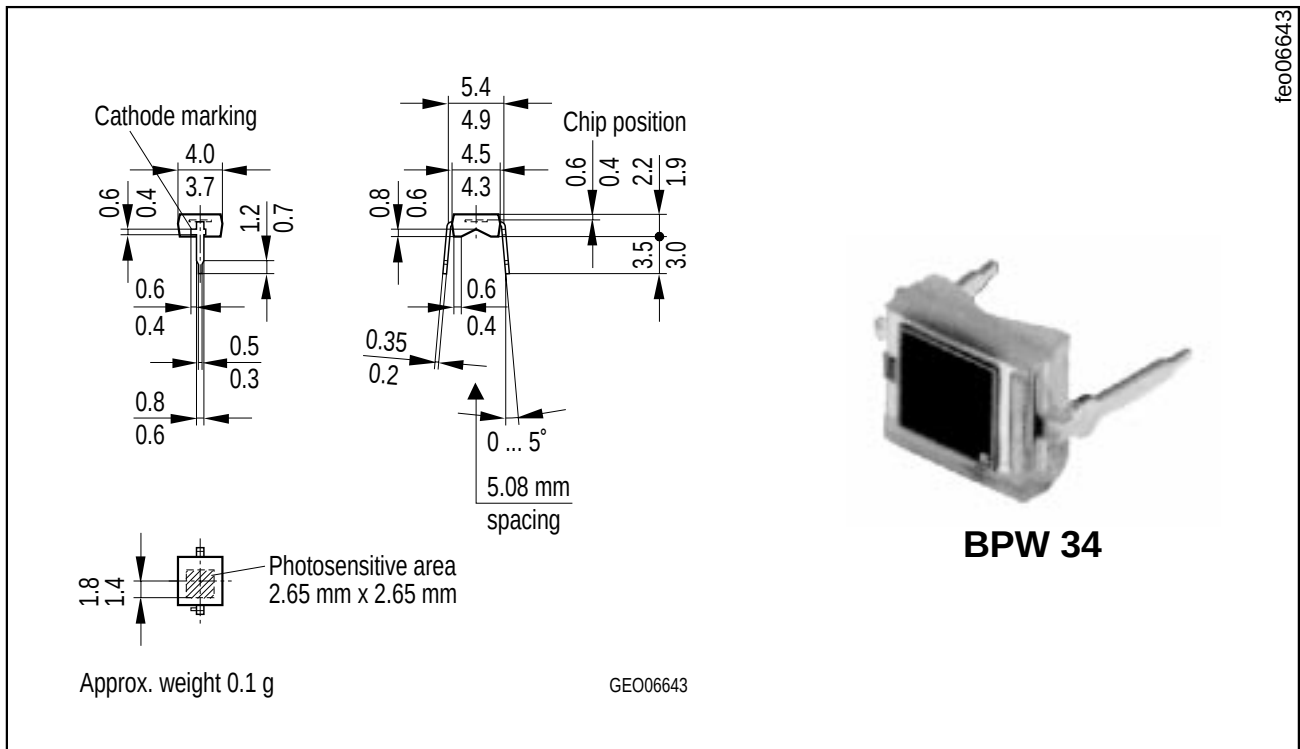


Silizium-PIN-Fotodiode
NEU: in SMT und als Reverse Gullwing
Silicon PIN Photodiode
NEW: in SMT and as Reverse Gullwing

BPW 34
BPW 34 S
BPW 34 S (E9087)



Maße in mm, wenn nicht anders angegeben/Dimensions in mm, unless otherwise specified.

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm
- Kurze Schaltzeit (typ. 20 ns)
- DIL-Plastikbauform mit hoher Packungsdichte
- BPW 34 S/(E9087): geeignet für Vapor-Phase Löten und IR-Reflow Löten (JEDEC level 4)

Anwendungen

- Lichtschranken für Gleich- und Wechsellichtbetrieb
- IR-Fernsteuerungen
- Industrieelektronik
- "Messen/Steuern/Regeln"

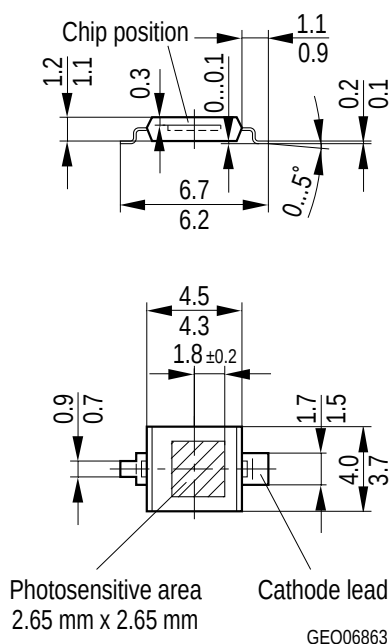
Features

- Especially suitable for applications from 400 nm to 1100 nm
- Short switching time (typ. 20 ns)
- DIL plastic package with high packing density
- BPW 34 S/(E9087): suitable for vapor-phase and IR-reflow soldering (JEDEC level 4)

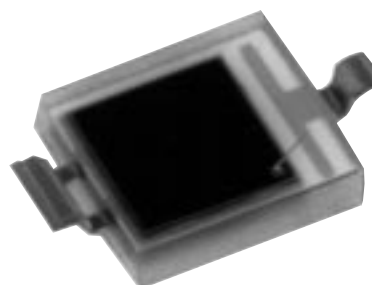
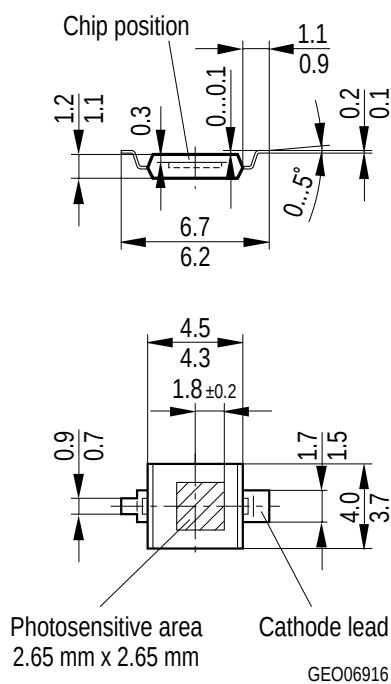
Applications

- Photointerrupters
- IR remote controls
- Industrial electronics
- For control and drive circuits

feo06862



BPW 34 S



BPW 34 S (E9087)

BPW34S

Maße in mm, wenn nicht anders angegeben/Dimensions in mm, unless otherwise specified.

Typ Type	Bestellnummer Ordering Code
BPW 34	Q62702-P73
BPW 34 S	Q62702-P1602
BPW 34 S (E9087)	Q62702-P1790

Grenzwerte Maximum Ratings

Bezeichnung Description	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 85	°C
Sperrspannung Reverse voltage	V_R	32	V
Verlustleistung, $T_A = 25\text{ °C}$ Total power dissipation	P_{tot}	150	mW

Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$) Characteristics ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$)

Bezeichnung Description	Symbol Symbol	Wert Value	Einheit Unit
Fotoempfindlichkeit, $V_R = 5\text{ V}$ Spectral sensitivity	S	80 (≥ 50)	nA/lx
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	850	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\text{ %}$ von S_{max} Spectral range of sensitivity $S = 10\text{ %}$ of S_{max}	λ	400 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	7.00	mm ²
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	2.65×2.65	mm × mm
Halbwinkel Half angle	φ	± 60	Grad deg.
Dunkelstrom, $V_R = 10\text{ V}$ Dark current	I_R	2 (≤ 30)	nA
Spektrale Fotoempfindlichkeit, $\lambda = 850\text{ nm}$ Spectral sensitivity	S_λ	0.62	A/W
Quantenausbeute, $\lambda = 850\text{ nm}$ Quantum yield	η	0.90	<u>Electrons</u> Photon
Leerlaufspannung, $E_v = 1000\text{ lx}$ Open-circuit voltage	V_o	365 (≥ 300)	mV

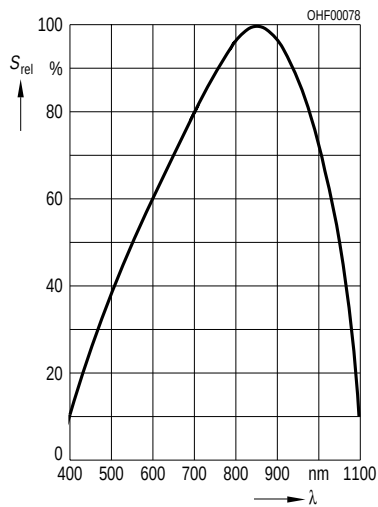
Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$)

Characteristics ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$) (cont'd)

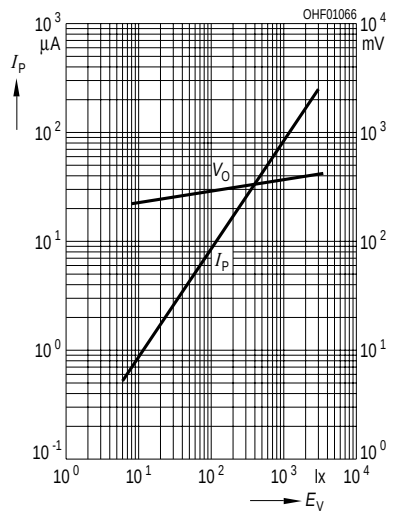
Bezeichnung Description	Symbol Symbol	Wert Value	Einheit Unit
Kurzschlußstrom, $E_v = 1000\text{ lx}$ Short-circuit current	I_{SC}	80	μA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 50\text{ }\Omega$; $V_R = 5\text{ V}$; $\lambda = 850\text{ nm}$; $I_p = 800\text{ }\mu\text{A}$	t_r, t_f	20	ns
Durchlaßspannung, $I_F = 100\text{ mA}$, $E = 0$ Forward voltage	V_F	1.3	V
Kapazität, $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_0	72	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	- 2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC}	TC_I	0.18	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10\text{ V}$, $\lambda = 850\text{ nm}$	NEP	4.1×10^{-14}	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 10\text{ V}$, $\lambda = 850\text{ nm}$ Detection limit	D^*	6.6×10^{12}	$\frac{\text{cm} \cdot \sqrt{\text{Hz}}}{\text{W}}$

Relative spectral sensitivity

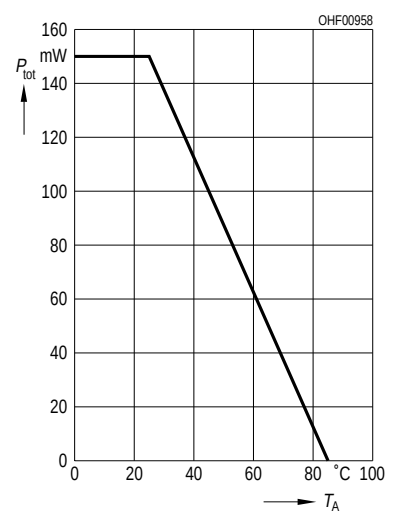
$$S_{\text{rel}} = f(\lambda)$$



Photocurrent $I_P = f(E_V), V_R = 5 \text{ V}$
Open-circuit voltage $V_O = f(E_V)$

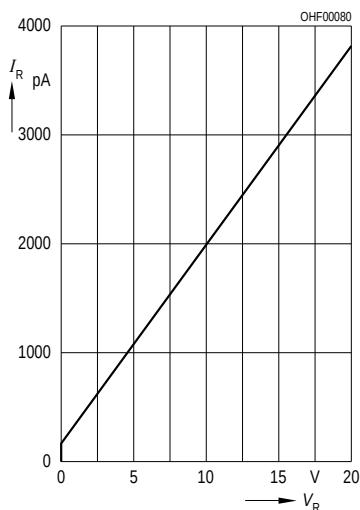


Total power dissipation $P_{\text{tot}} = f(T_A)$



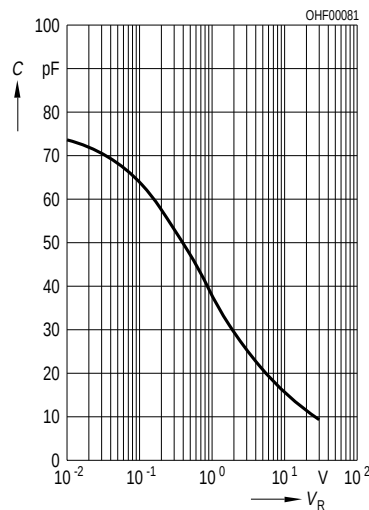
Dark current

$$I_R = f(V_R), E = 0$$



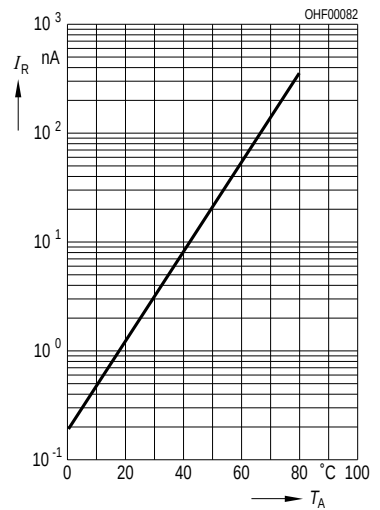
Capacitance

$$C = f(V_R), f = 1 \text{ MHz}, E = 0$$



Dark current

$$I_R = f(T_A), V_R = 10 \text{ V}, E = 0$$



Directional characteristics $S_{\text{rel}} = f(\phi)$

